



Stud Diode

Avalanche Diode

SKNa 202

Publish Data

Features

- Avalanche type reverse characteristic
- Reverse voltages up to 5000 V
- Hermetic metal case with ceramic insulator and extra long creepage distances
- Threaded stud ISO M16 x 1,5
- Cooling via heatsinks
- SKN: Anode to stud

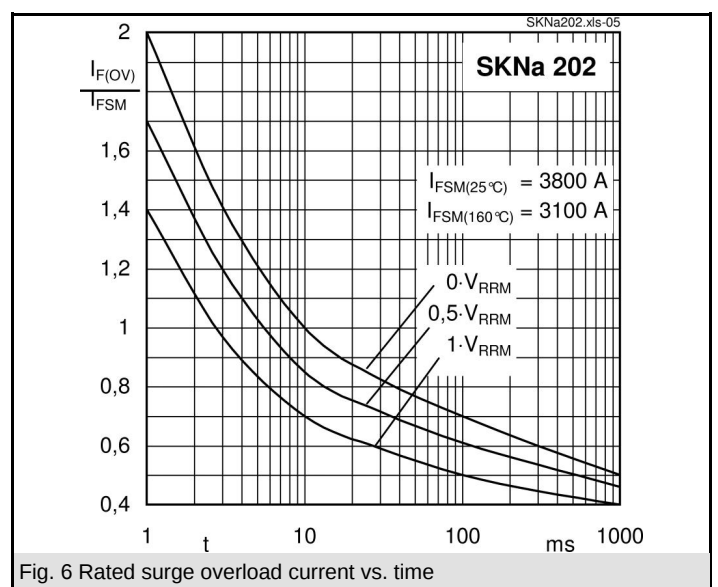
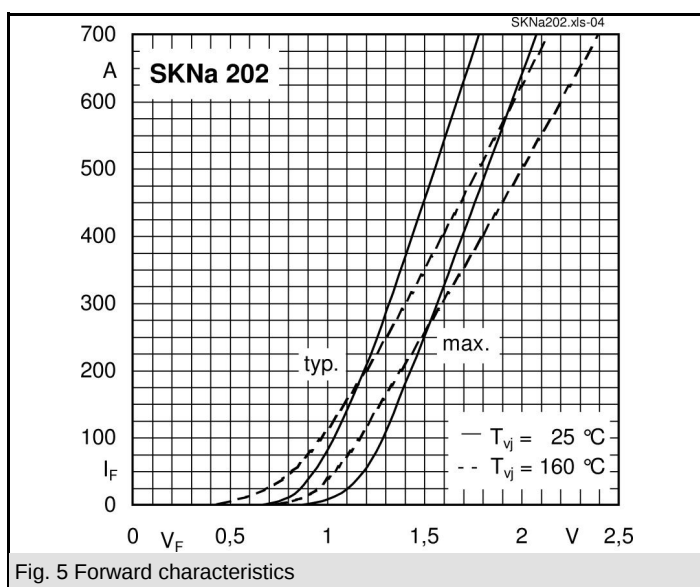
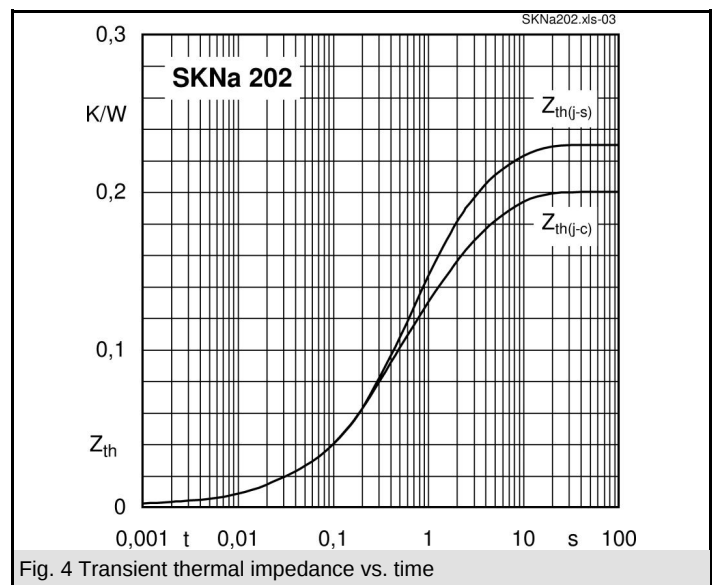
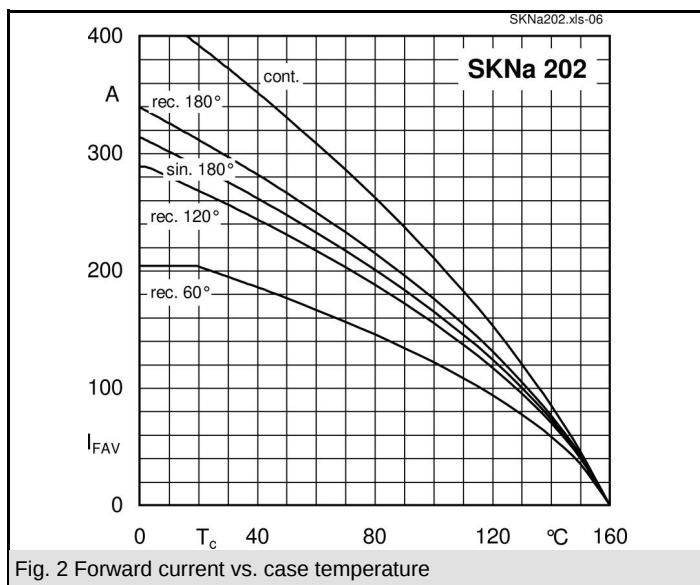
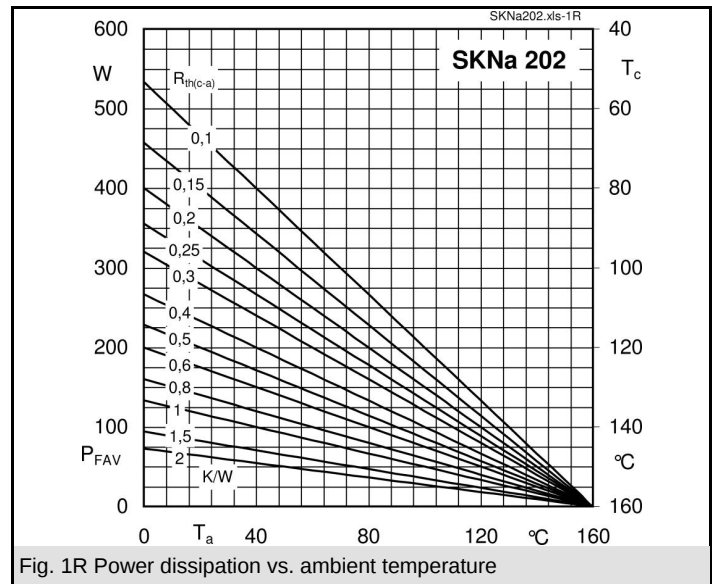
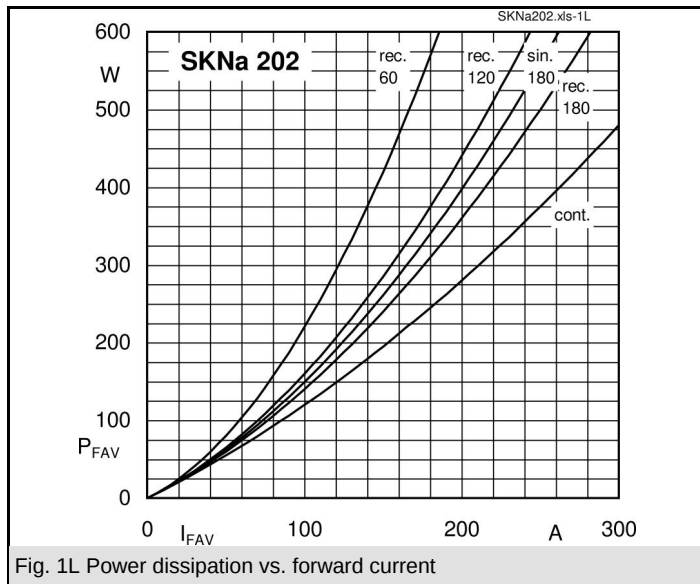
Typical Applications

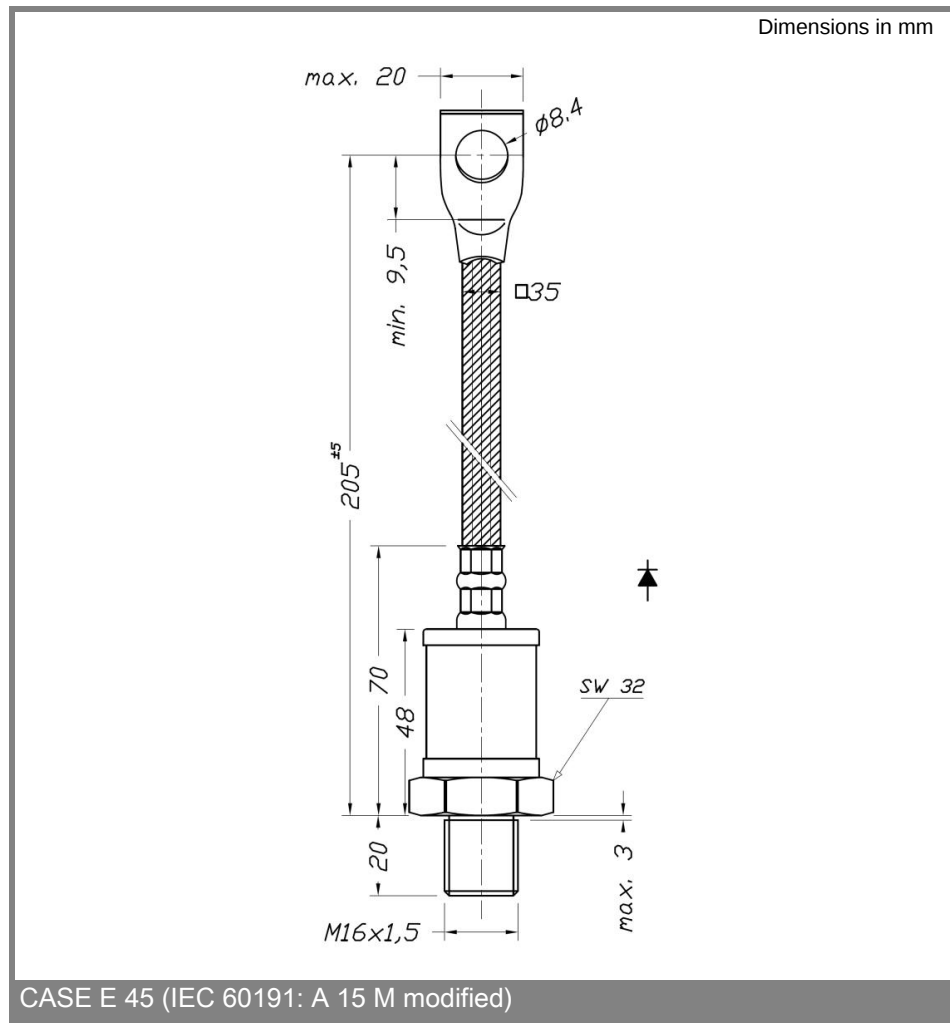
- High voltage rectifier diode for traction and heavy duty applications
- Series connections for high voltage applications
- Non-controllable and half-controllable rectifiers
- Free-wheeling diodes

$V_{(BR)min}$	$I_{FRMS} = 500 A$ (maximum value for continuous operation)	C_{max}	R_{min}
V	$I_{FAV} = 200 A$ (sin. 180; $T_c = 80 ^\circ C$)	μF	Ω
3600	SKNa 202/36		
4000	SKNa 202/40		
4200	SKNa 202/42		
4500	SKNa 202/45		
4600	SKNa 202/46		
4800	SKNa 202/48		
5000	SKNa 202/50		

Symbol	Conditions	Values	Units
I_{FAV}	sin. 180 ; $T_c = 80$ (100) $^\circ C$	200 (165)	A
I_D	K 0,55; $T_a = 45 ^\circ C$; B2 / B6 K 0,55F; $T_a = 35 ^\circ C$; B2 / B6	208 / 296 340 / 478	A A
I_{FSM}	$T_{vj} = 25 ^\circ C$; 10 ms $T_{vj} = 160 ^\circ C$; 10 ms	3800 3100	A A
i^2t	$T_{vj} = 25 ^\circ C$; 8,3 ... 10 ms $T_{vj} = 160 ^\circ C$; 8,3 ... 10 ms	72000 48000	A ² s A ² s
V_F	$T_{vj} = 25 ^\circ C$; $I_F = 600 A$	max. 1,95	V
$V_{(TO)}$	$T_{vj} = 150 ^\circ C$	max. 1	V
r_T	$T_{vj} = 150 ^\circ C$	max. 2	m Ω
I_{RD}	$T_{vj} = 25 ^\circ C$; $V_{RD} = V_{(BR)min}$ $T_{vj} = 160 ^\circ C$; $V_{RD} = V_{(BR)min}$;	max. 2000 max. 35	μA mA
P_{RSM}	$T_{vj} = 160 ^\circ C$; $t_p = 10 \mu s$	60	kW
$R_{th(j-c)}$		0,2	K/W
$R_{th(c-s)}$		0,03	K/W
T_{vj}		- 40 ... + 160	$^\circ C$
T_{stg}		- 40 ... + 160	$^\circ C$
V_{isol}		-	V~
M_s	to heatsink	30 270	Nm lb.in.
a		5 * 9,81	m/s ²
m	approx.	260	g
Case		E 45	







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